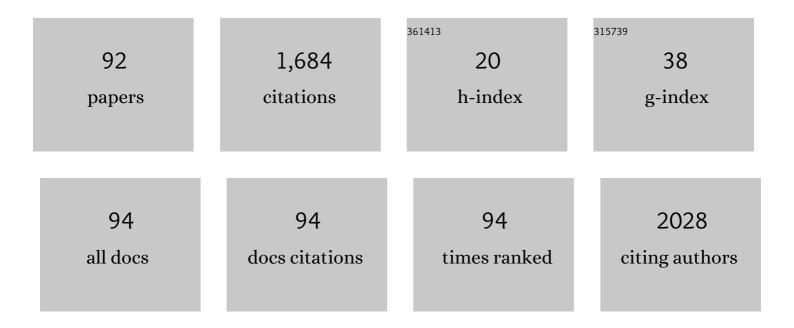
Sergi HernÃ;ndez

List of Publications by Year in descending order

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SEDCI HEDNÃ:NDEZ

#	Article	IF	CITATIONS
1	Ultrafast All-Optical Switching in a Silicon-Nanocrystal-Based Silicon Slot Waveguide at Telecom Wavelengths. Nano Letters, 2010, 10, 1506-1511.	9.1	218
2	Effect of curing cycle on void distribution and interlaminar shear strength in polymer-matrix composites. Composites Science and Technology, 2011, 71, 1331-1341.	7.8	131
3	Optimization of curing cycle in carbon fiber-reinforced laminates: Void distribution and mechanical properties. Composites Science and Technology, 2013, 85, 73-82.	7.8	101
4	Raman-scattering study of the InGaN alloy over the whole composition range. Journal of Applied Physics, 2005, 98, 013511.	2.5	93
5	Linear and nonlinear optical properties of Si nanocrystals in SiO2 deposited by plasma-enhanced chemical-vapor deposition. Journal of Applied Physics, 2008, 103, .	2.5	78
6	Silicon nanocluster crystallization in SiOx films studied by Raman scattering. Journal of Applied Physics, 2008, 104, .	2.5	71
7	Optical energies of AlInN epilayers. Journal of Applied Physics, 2008, 103, .	2.5	58
8	Far-infrared transmission in GaN, AlN, and AlGaN thin films grown by molecular beam epitaxy. Journal of Applied Physics, 2008, 104, 033544.	2.5	43
9	Determining the crystalline degree of silicon nanoclusters/SiO2 multilayers by Raman scattering. Journal of Applied Physics, 2014, 115, .	2.5	39
10	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. Applied Physics Letters, 2003, 83, 3069-3071.	3.3	36
11	Up-conversion effect of Er- and Yb-doped ZnO thin films. Thin Solid Films, 2014, 562, 456-461.	1.8	36
12	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. Applied Physics Letters, 2000, 77, 3556-3558.	3.3	34
13	Silicon nanocrystals in carbide matrix. Solar Energy Materials and Solar Cells, 2014, 128, 138-149.	6.2	34
14	Pushing the Composition Limit of Anisotropic Ge _{1–<i>x</i>} Sn _{<i>x</i>} Nanostructures and Determination of Their Thermal Stability. Chemistry of Materials, 2017, 29, 9802-9813.	6.7	33
15	Raman scattering by LO phonon-plasmon coupled modes inn-typeIn0.53Ga0.47As. Physical Review B, 2001, 65, .	3.2	31
16	Blue luminescence at room temperature in defective MgO films. Solid State Communications, 2011, 151, 751-753.	1.9	28
17	Charge transport and electroluminescence of silicon nanocrystals/SiO2 superlattices. Journal of Applied Physics, 2013, 114, .	2.5	27
18	High-pressure Raman scattering in bulk HfS2: comparison of density functional theory methods in layered MS2 compounds (M = Hf, Mo) under compression. Scientific Reports, 2018, 8, 12757.	3.3	26

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19	Direct observation of LO phonon-plasmon coupled modes in the infrared transmission spectra ofn-GaAs andnâ^'InxGa1â^'xAsepilayers. Physical Review B, 2004, 69, .	3.2	25
20	Annealing temperature and barrier thickness effect on the structural and optical properties of silicon nanocrystals/SiO2 superlattices. Journal of Applied Physics, 2014, 116, 133505.	2.5	24
21	Structural and optical properties of dilute InAsN grown by molecular beam epitaxy. Journal of Applied Physics, 2010, 108, .	2.5	20
22	Probing the intermixing in In(Ga)Asâ^•GaAs self-assembled quantum dots by Raman scattering. Journal of Applied Physics, 2006, 99, 043501.	2.5	19
23	Structural, optical and electrical properties of silicon nanocrystals embedded in SixC1â^²x/SiC multilayer systems for photovoltaic applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 639-644.	3.5	19
24	Retrieving the electronic properties of silicon nanocrystals embedded in a dielectric matrix by low-loss EELS. Nanoscale, 2014, 6, 14971-14983.	5.6	18
25	High Quality Inkjet Printedâ€Emissive Nanocrystalline Perovskite CsPbBr ₃ Layers for Color Conversion Layer and LEDs Applications. Advanced Materials Technologies, 2022, 7, .	5.8	18
26	The Design of a Chain of Spherical Stephenson Mechanisms for a Gearless Robotic Pitch-Roll Wrist. Journal of Mechanical Design, Transactions of the ASME, 2006, 128, 422-429.	2.9	17
27	Structural and optical characterization of size controlled silicon nanocrystals in SiO2/SiOxNy multilayers. Energy Procedia, 2011, 10, 43-48.	1.8	16
28	Organosilane-functionalization of nanostructured indium tin oxide films. Interface Focus, 2016, 6, 20160056.	3.0	16
29	Influence of post annealing treatments on the luminescence of rare earth ions in ZnO:Tb,Eu/Si heterojunction. Applied Surface Science, 2021, 556, 149754.	6.1	16
30	Lattice dynamics study of cubic Tb ₂ O ₃ . Journal of Raman Spectroscopy, 2018, 49, 2021-2027.	2.5	15
31	Silicon nanocrystals from highâ€ŧemperature annealing: Characterization on device level. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 669-675.	1.8	14
32	Electro-optical Properties of Non-stoichiometric Silicon Nitride Films for Photovoltaic Applications. Energy Procedia, 2014, 44, 145-150.	1.8	14
33	Structural parameters effect on the electrical and electroluminescence properties of silicon nanocrystals/SiO2 superlattices. Nanotechnology, 2015, 26, 185704.	2.6	13
34	Abellaite, NaPb2 (CO3)2 (OH), a new supergene mineral from the Eureka mine, Lleida province, Catalonia, Spain. European Journal of Mineralogy, 2017, 29, 915-922.	1.3	13
35	Toward RGB LEDs based on rare earth-doped ZnO. Nanotechnology, 2020, 31, 465207.	2.6	13
36	Resistive switching and charge transport mechanisms in ITO/ZnO/ <i>p</i> -Si devices. Applied Physics Letters, 2018, 113, .	3.3	12

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37	Activation of visible up-conversion luminescence in transparent and conducting ZnO:Er:Yb films by laser annealing. Journal of Luminescence, 2015, 167, 101-105.	3.1	11
38	Memristive behaviour of Si-Al oxynitride thin films: the role of oxygen and nitrogen vacancies in the electroforming process. Nanotechnology, 2018, 29, 235702.	2.6	11
39	Evidence of phosphorus incorporation into InGaAs/InP epilayers after thermal annealing. Journal of Applied Physics, 2003, 93, 9019-9023.	2.5	10
40	Silicon nanocrystals embedded in silicon carbide as a wide-band gap photovoltaic material. Solar Energy Materials and Solar Cells, 2016, 144, 551-558.	6.2	10
41	Light-activated electroforming in ITO/ZnO/ <i>p</i> -Si resistive switching devices. Applied Physics Letters, 2019, 115, .	3.3	10
42	Extended X-ray absorption fine structure studies of thulium doped GaN epilayers. Superlattices and Microstructures, 2004, 36, 729-736.	3.1	9
43	Extended X-ray absorption fine structure studies of GaN epilayers doped with Er. Optical Materials, 2006, 28, 785-789.	3.6	9
44	Comparative study of Si precipitation in silicon-rich oxide films. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 990-993.	2.7	9
45	Comparative study of the nonlinear optical properties of Si nanocrystals fabricated by eâ€beam evaporation, PECVD or LPCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 969-973.	0.8	9
46	Tailoring the surface density of silicon nanocrystals embedded in SiOx single layers. Journal of Applied Physics, 2013, 114, 233101.	2.5	9
47	Optical emission from <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Si</mml:mi><mml:msub><mml:mi mathvariant="normal">O<mml:mn>2</mml:mn></mml:mi </mml:msub></mml:mrow>-embedded silicon nanocrystals: A high-pressure Raman and photoluminescence study. Physical Review B, 2015, 92,</mml:math 	3.2	9
48	Investigation on the structural changes of ZnO:Er:Yb thin film during laser annealing to fabricate a transparent conducting upconverter. Journal of Luminescence, 2017, 185, 112-119.	3.1	9
49	Effect of Si ₃ N ₄ â€Mediated Inversion Layer on the Electroluminescence Properties of Silicon Nanocrystal Superlattices. Advanced Electronic Materials, 2018, 4, 1700666.	5.1	9
50	Structural and High-Pressure Properties of Rheniite (ReS2) and (Re,Mo)S2. Minerals (Basel,) Tj ETQq0 0 0 rgBT /Ov	verlack 10 2.8ck	Tf 50 222 T
51	Optical properties of high-temperature annealed Eu-implanted GaN. Optical Materials, 2006, 28, 797-801.	3.6	8
52	Silicon nanocrystals-based electroluminescent resistive switching device. Journal of Applied Physics, 2019, 126, .	2.5	8
53	Study of the electrical activation of Si+-implanted InGaAs by means of Raman scattering. Journal of Applied Physics, 2003, 93, 2659-2662.	2.5	7
54	Electrochemical characterization of organosilane-functionalized nanostructured ITO surfaces. Applied Physics Letters, 2016, 109, 063109.	3.3	7

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55	Discrimination of polar order extent in BaZr x Ti 1-x O 3 epitaxial thin films by Raman spectroscopy. Applied Surface Science, 2017, 424, 374-377.	6.1	7
56	Lattice order in thulium-doped GaN epilayers: In situ doping versus ion implantation. Optical Materials, 2006, 28, 771-774.	3.6	6
57	Electrical and Optical Characterisation of Silicon Nanocrystals Embedded in SiC. Solid State Phenomena, 0, 205-206, 480-485.	0.3	6
58	Modulation of the electroluminescence emission from ZnO/Si NCs/ <i>p</i> -Si light-emitting devices via pulsed excitation. Applied Physics Letters, 2017, 110, .	3.3	6
59	Lattice damage study of implanted InGaAs by means of Raman spectroscopy. Journal of Luminescence, 2000, 87-89, 721-723.	3.1	5
60	Non-Linear Optical Properties of Si Nanocrystals. , 2006, , .		5
61	Two-photon absorption in Si-nanocrystals deposited by plasma-enhanced chemical-vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 1002-1005.	2.7	5
62	Structural and optical properties of MOCVD InAlN epilayers. Materials Research Society Symposia Proceedings, 2005, 892, 502.	0.1	4
63	Optical nonlinearities in Si-nanocrystals at 1064 nm excited by nanosecond-pulses. Journal of Applied Physics, 2010, 108, .	2.5	4
64	Structural and optical properties of Al-Tb/SiO2 multilayers fabricated by electron beam evaporation. Journal of Applied Physics, 2016, 120, .	2.5	4
65	Heterogeneous distribution of B-site cations in BaZrxTi1â^'xO3 epitaxial thin films grown on (001) SrTiO3 by pulsed laser deposition. Applied Surface Science, 2016, 381, 12-16.	6.1	4
66	Pathways of carrier recombination in Si/SiO2 nanocrystal superlattices. Journal of Applied Physics, 2019, 126, 163101.	2.5	4
67	The composition dependence of the optical properties of InN-rich InGaN grown by MBE. Materials Research Society Symposia Proceedings, 2004, 831, 479.	0.1	3
68	Non linear optical properties of Silicon nanocrystals for applications in photonic logic gates devices. , 2008, , .		3
69	Bulk silica-based luminescent materials by sol-gel processing of non-conventional precursors. Applied Physics Letters, 2012, 101, 171908.	3.3	3
70	New strategies in laser processing of TCOs for light management improvement in thin-film silicon solar cells. Proceedings of SPIE, 2014, , .	0.8	3
71	Transparent Conducting Oxides for Optoelectronics and Biosensing Applications. , 2018, , .		3
72	Nonlinear Optical Properties of Si Nanocrystals. Materials Research Society Symposia Proceedings, 2006, 958, 1.	0.1	2

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73	High quality coupled ring resonators based on silicon clusters slot waveguide. , 2008, , .		2
74	Observation of Room Temperature Photoluminescence from Asymmetric CuGaO ₂ /ZnO/ZnMgO Multiple Quantum Well <i>Structures</i> . Journal of Nanoscience and Nanotechnology, 2015, 15, 3944-3950.	0.9	2
75	Size ontrolled Si Nanocrystals Fabricated by Electron Beam Evaporation. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800619.	1.8	2
76	Photoelectrical reading in ZnO/Si NCs/p-Si resistive switching devices. Applied Physics Letters, 2020, 116, 193503.	3.3	2
77	Ultraviolet, visible and near infrared photoresponse of SiO2/Si/SiO2 multilayer system into a MOS capacitor. Materials Science in Semiconductor Processing, 2021, 134, 106009.	4.0	2
78	UV-Raman scattering study of lattice recovery by thermal annealing of Eu+ -implanted GaN layers. Superlattices and Microstructures, 2006, 40, 440-444.	3.1	1
79	Raman scattering and cathodoluminescence characterization of near lattice-matched InxAl1â^'xN epilayers. Semiconductor Science and Technology, 2008, 23, 105002.	2.0	1
80	Effect of the annealing treatments on the transport and electroluminescence properties of SiO2 layers doped with Er and Si nanoclusters Materials Research Society Symposia Proceedings, 2011, 1289, 511.	0.1	1
81	Luminescence yield in Al and Tb3+delta-doped oxide thin films fabricated by electron beam evaporation. , 2015, , .		1
82	Green Electroluminescence of Al/Tb/Al/SiO ₂ Devices Fabricated by Electron Beam Evaporation. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700451.	1.8	1
83	Electroforming of Si NCs/p-Si photovoltaic devices: Enhancement of the conversion efficiency through resistive switching. Solar Energy Materials and Solar Cells, 2021, 230, 111252.	6.2	1
84	MICRO-RAMAN STUDY OF SURFACE ALTERATIONS IN InGaAs AFTER THERMAL ANNEALING TREATMENTS. International Journal of Modern Physics B, 2002, 16, 4401-4404.	2.0	0
85	Extended X-ray Absorption Fine Structure Studies of InGaN Epilayers. Materials Research Society Symposia Proceedings, 2004, 831, 421.	0.1	0
86	X-ray Excited Optical Luminescence Studies of InGaN and Rare-Earth Doped GaN Epilayers. Materials Research Society Symposia Proceedings, 2004, 831, 426.	0.1	0
87	Anomalous dispersion with excitation wavelength of longitudinal optical phonon–plasmon coupled modes in n-InGaAs. Journal of Physics Condensed Matter, 2004, 16, 971-978.	1.8	0
88	Non-linear optical properties of PECVD Si-nc under nanosecond excitation. , 2007, , .		0
89	Quantum phenomena during electron transport in InAs nanowires. , 2010, , .		0
90	Electrical and electroluminescence properties of silicon nanocystals/SiO ₂ superlattices. Proceedings of SPIE, 2014, , .	0.8	0

#	Article	IF	CITATIONS
91	(Invited) Transport and Electroluminescence Properties of Size-Controlled Silicon Nanocrystals Embedded in SiO2 Matrix Following the Superlattice Approach. ECS Transactions, 2014, 61, 133-139.	0.5	ο
92	Investigating the electro-optical properties of non-stoichiometric silicon nitride thin films for photovoltaic applications. Optica Pura Y Aplicada, 2013, 46, 309-314.	0.1	0